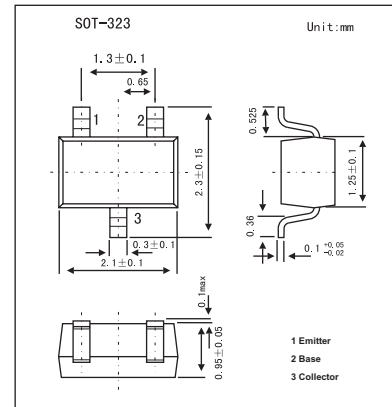


Silicon PNP Epitaxial

2SA1588

■ Features

- Excellent hFE linearity.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-35	V
Collector-emitter voltage	V _{CEO}	-30	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-500	mA
Base current	I _B	-50	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _J	125	°C
Storage temperature range	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol		Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} =-35V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-100mA	70		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA		-0.1	-0.3	V
Transition frequency	f _T	V _{CE} =-1V, I _C =-100mA	80			MHz
Collector output capacitance	C _{ob}	V _{CE} =-6V, I _C =-20mA		4	7	pF
Noise figure	N _F	V _{CB} =-6V, I _E =0, f=1MHz		1.0	10	dB

■ hFE Classification

Marking	ZO	ZY
hFE	70~140	120~240